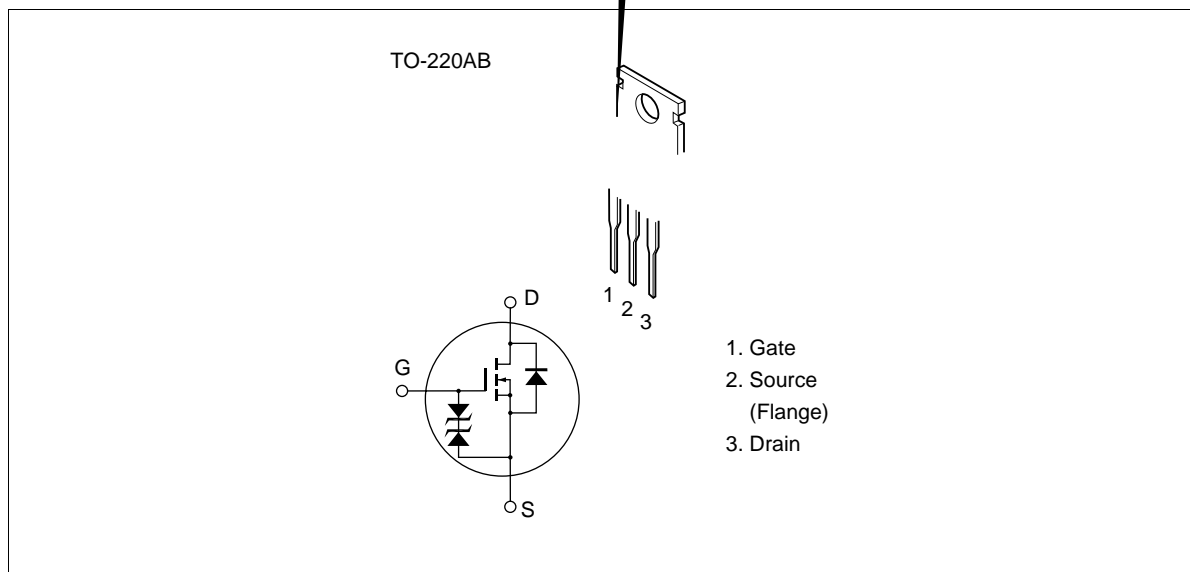


# 2SK213, 2SK214, 2SK215, 2SK216

Silicon N-Channel MOS FET

## HITAC I



# 2SK213, 2SK214, 2SK215, 2SK216

## Absolute Maximum Ratings (Ta = 25°C)

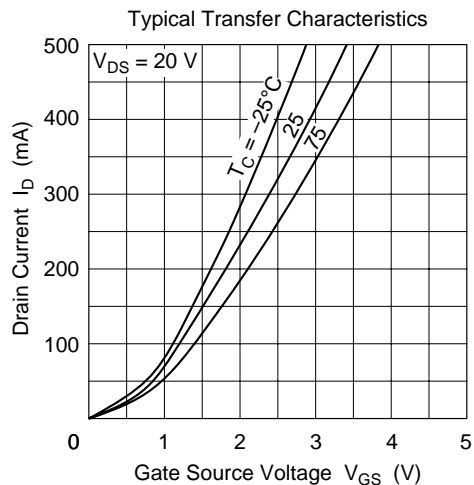
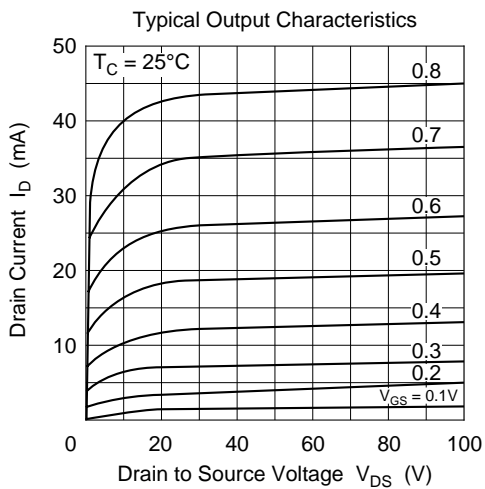
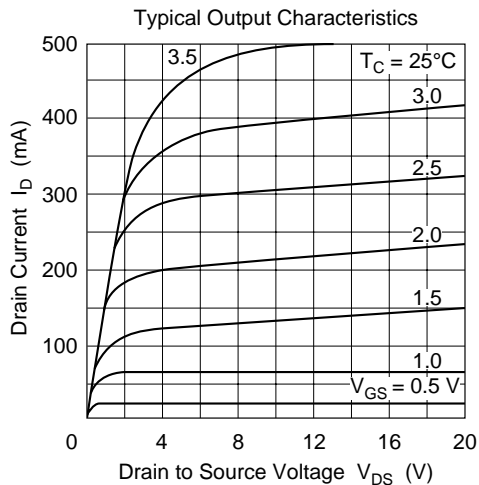
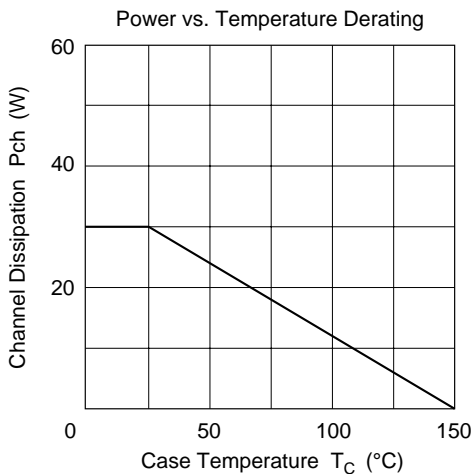
Item		Symbol	Rated	Unit
Drain to source voltage	2SK213	$V_{DSX}$	140	V
	2SK214		160	
	2SK215		180	
	2SK216		200	
Gate to source voltage		$V_{GSS}$	±15	V
Drain current		$I_D$	500	mA
Body to drain diode reverse drain current		$I_{DR}$	500	mA
Channel dissipation		Pch	1.75	W
		$Pch^{*1}$	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-45 to +150	°C

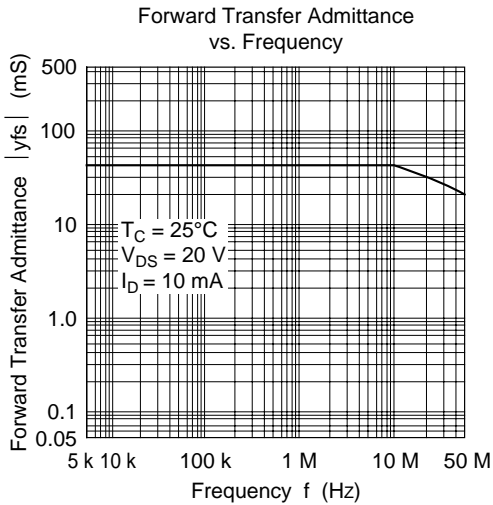
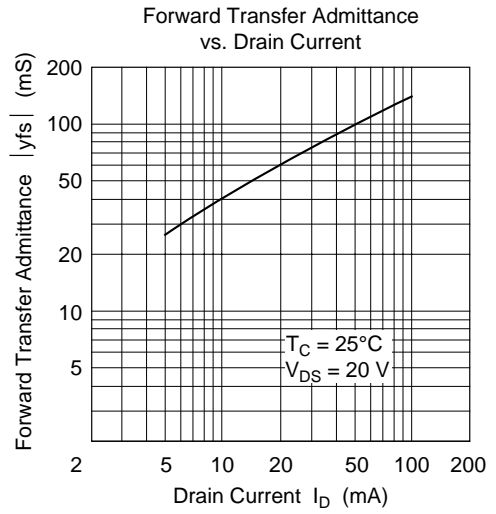
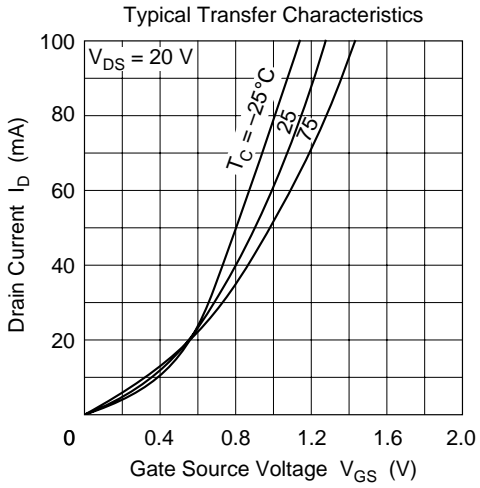
Note: 1. Value at  $T_C = 25^\circ\text{C}$

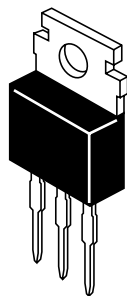
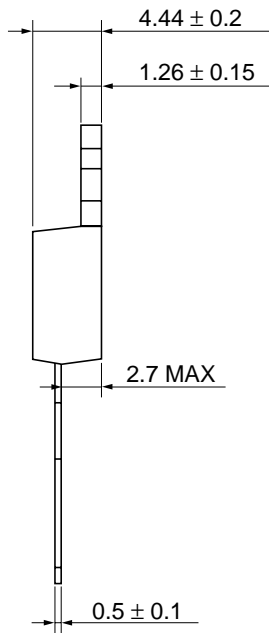
## Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK213	$V_{(BR)DSX}$	140	—	—	V	$I_D = 1 \text{ mA}, V_{GS} = -2 \text{ V}$
	2SK214		160	—	—	V	
	2SK215		180	—	—	V	
	2SK216		200	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	±15	—	—	V	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0$
Gate to source voltage		$V_{GS(on)}$	0.2	—	1.5	V	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V}^{*1}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	2.0	V	$I_D = 10 \text{ mA}, V_{GD} = 0^{*1}$
Forward transfer admittance		$ y_{fs} $	20	40	—	mS	$I_D = 10 \text{ mA}, V_{DS} = 20 \text{ V}^{*1}$
Input capacitance		Ciss	—	90	—	pF	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V},$
Reverse transfer capacitance		Crss	—	2.2	—	pF	$f = 1 \text{ MHz}$

Note: 1. Pulse test







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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